

SILICON PHOTODIODE CHIPS

DEVICE NO. : PD-0080

1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-0080

2. Structure :

2-1. Planar type : PIN diode.

2-2. Electrodes :

Top side (Anode) : Aluminum alloy .

Back side (Cathode) : Gold alloy.

3. Size :

3-1. Chip size : 80 mils × 80 mils (2.030 mm × 2.030 mm).

3-2. Chip thickness : 12 ± 1.5 mils (0.305 ± 0.038 mm).

3-3. Active area : 70 mils × 70 mils (1.780 mm × 1.780 mm).

3-4. Bonding pad (anode) : 6 mils (0.150 mm) diameter.

3-5. Pattern drawing : refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse dark Current	ID	VR=10V H=0mw/cm ²		5	30	nA
Reverse breakdown voltage	V (BR) R	IR=100μA H=0mw/cm ²	33	170		V
Open circuit Voltage	Voc	CT=2870 ° K H=5mw/cm ²		390		mV
Short circuit Current	Isc	CT=2870 ° K H=5mw/cm ²	23	28		μA
Reverse light Current	IL	VR =5V CT=2870 ° K H=5mw/cm ²	23	28		μA
Total Capacitance	Ct	VR =5V H=0mw/cm ² f=1MHz		12		pF
Turn-on/ Turn-off time	ton/toff	VR=10V RL=1000Ω		25/25		nS

